

IN THE SPECIFICATION:

Please change the title to:

Fabrication Of Ultra Shallow Junctions From A Solid Source With Fluorine
Implantation

IN THE CLAIMS:

Please enter the following clean version of amend Claim 4:

Sub B7 4. The method of claim 1, wherein after heating 90% of that portion of the dopant
that has diffused into the semiconductor substrate is located within about 50 nm from
the surface of the semiconductor substrate.